

< C band internally matched power GaAs FET >

MGFC39V7177A

7.1 – 7.7 GHz BAND / 8W

DESCRIPTION

The MGFC39V7177A is an internally impedance-matched GaAs power FET especially designed for use in 7.1 - 7.7 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

FEATURES

Class A operation

Internally matched to 50(ohm) system • High output power

- P1dB=8W (TYP.) @f=7.1 7.7GHz • High power gain
- GLP= 8.0dB (TYP.) @f=7.1 7.7GHz • High power added efficiency
- P.A.E.=28% (TYP.) @f=7.1 7.7GHz • Low distortion [item -51]
- IM3=-45dBc (TYP.) @Po=28dBm S.C.L

APPLICATION

- item 01 : 7.1 7.7 GHz band power amplifier
- \bullet item 51 : 7.1 7.7 GHz band digital radio communication

• IG

RECOMMENDED BIAS CONDITIONS

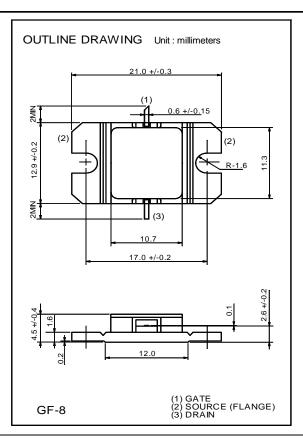
VDS=10V
ID=2.4A
Refer to Bias Procedure
RG=50ohm

Absolute maximum ratings (Ta=25°C)

Symbol	Parameter	Ratings	Unit				
VGDO	Gate to drain breakdown voltage	-15	V				
VGSO	Gate to source breakdown voltage	-15	V				
ID	Drain current	7.5	А				
IGR	Reverse gate current	-20	mA				
IGF	Forward gate current	42	mA				
PT *1	Total power dissipation	42.8	W				
Tch	Cannel temperature	175	°C				
Tstg	Storage temperature	-65 to +175	°C				
*1 · T- 0500							

*1 : Tc=25°C

Electrical characteristics (Ta=25°C)



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Symbol	Parameter	Test conditions	Limits		Unit	
			Min.	Тур.	Max.	
IDSS	Saturated drain current	VDS=3V,VGS=0V	-	-	7.5	А
gm	Transconductance	VDS=3V,ID=2.2A	-	2	-	S
VGS(off)	Gate to source cut-off voltage	VDS=3V,ID=20mA	-	-	-4.5	V
P1dB	Output power at 1dB gain compression	VDS=10V,ID(RF off)=2.4A	38	39.5	-	dBm
GLP	Linear Power Gain	f=7.1 – 7.7GHz	7	8	-	dB
ID	Drain current		-	-	3	А
P.A.E.	Power added efficiency		-	28	-	%
IM3 *2	3rd order IM distortion		-42	-45	-	dBc
Rth(ch-c) *3	Thermal resistance	delta Vf method	-	-	3.5	°C/W

*2 :item -51 ,2 tone test,Po=28dBm Single Carrier Level ,f=7.7GHz,delta f=10MHz

*3 :Channel-case

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